Description

The UE051006D is an uni-directional TVS diode,utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive high-speed data lines. The UE051006D has an ultra-low capacitance with a typical value at 0.6pF, and complies with the IEC 61000-4-2 (ESD) standard with ±25kV air and ±20kV contact discharge. It is assembled into an ultra-small 1.0 x 0.6 x 0.5mm lead-free DFN package. The small size, ultra-low capacitance and high ESD surge protection make UE051006D an ideal choice to protect cell phone, digital video interfaces and other high speed ports.

Features

- Ultra small package: 1.0 x0.6 x0.5mm
- Ultra low capacitance: 0.6pF typical
- Ultra low leakage：nA level
- Operating voltage：5V
- Low clamping voltage
- 3-pin leadless package
- Up to 2-line protects
- Complies with following standards:
  - IEC 61000-4-2 (ESD) immunity test
    - Air discharge: ±25kV
    - Contact discharge: ±20kV
  - IEC61000-4-5 (Lightning) 5A (8/20μs)
- RoHS Compliant

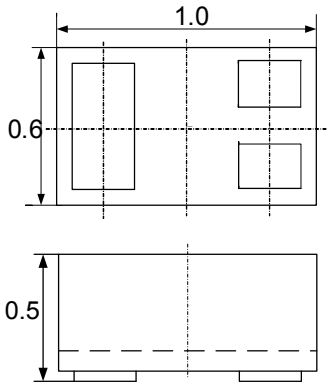
Mechanical Characteristics

- Package: DFN1006-3 (1.0 x0.6 x0.5mm)
- Lead Finish: NiPdAu
- Case Material: “Green” Molding Compound.
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminal Connections: See Diagram Below
- Marking Information: See Below

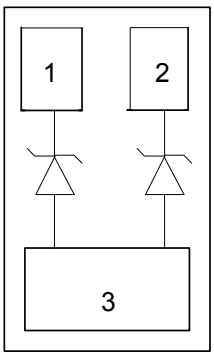
Applications

- Cellular Handsets and Accessories
- Display Ports
- MDDI Ports
- USB 2.0 and 3.0 Ports
- HDMI 1.3 and 1.4
- Digital Visual Interface(DVI)
- PCI Express and Serial SATA Ports
- Notebook Computer
- IEEE 1394

Dimensions and Pin Configuration

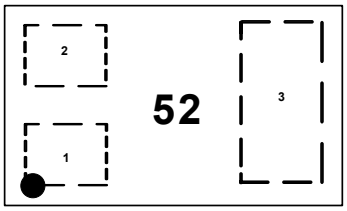


Package Dimensions



Circuit and Pin Schematic

Marking Information



52 = Device Marking Code
Dot denotes Pin1

Ordering Information

Part Number	Marking	Packaging	Reel Size
UE051006D	52	10000/Tape & Reel	7 inch

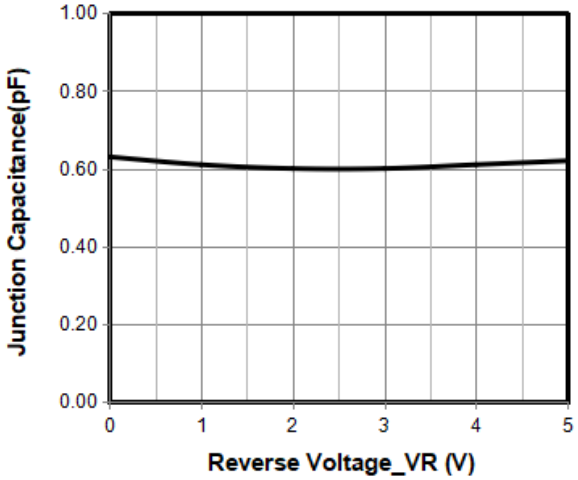
Absolute Maximum Ratings (T_A=25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power(8/20μs)	Ppk	75	W
Peak Pulse Current(8/20μs)	I_{PP}	5	A
ESD per IEC 61000−4−2 (Air) ESD per IEC 61000−4−2 (Contact)	V_{ESD}	±25 ±20	kV
Operating Temperature Range	T_J	−55 to +125	°C
Storage Temperature Range	Tstg	−55 to +125	°C

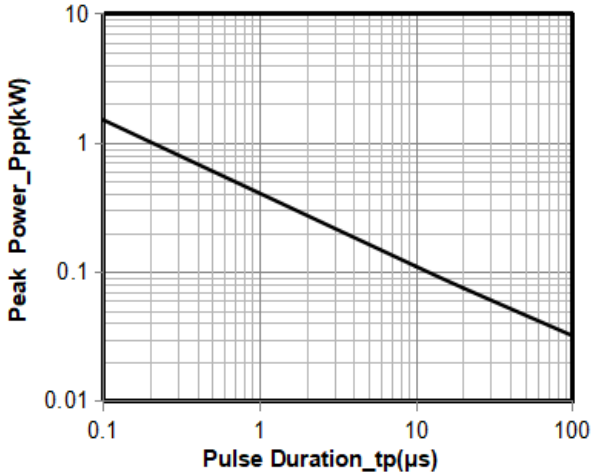
Electrical Characteristics (T_A=25°C unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	V_{RWM}			5	V	Pin 1 or pin 2 to pin 3 and between pin 1 and pin 2
Breakdown Voltage	V_{BR}	6			V	I_T = 1mA, pin 1 or pin 2 to pin 3 and between pin 1 and pin 2
Reverse Leakage Current	I_R			0.5	μA	V_{RWM} = 5V, Pin 1 or pin 2 to pin 3 and between pin 1 and pin 2
Clamping Voltage	V_C			10	V	I_{PP} = 1A (8 x 20μs pulse), pin 1 or pin 2 to pin 3
Clamping Voltage	V_C			15	V	I_{PP} = 5A (8 x 20μs pulse), pin 1 or pin 2 to pin 3
Junction Capacitance	C_J		0.3	0.5	pF	VR = 0V, f = 1MHz, between pin 1 and pin 2
Junction Capacitance	C_J			0.8	pF	VR = 0V, f = 1MHz, pin 1 or pin 2 to pin 3

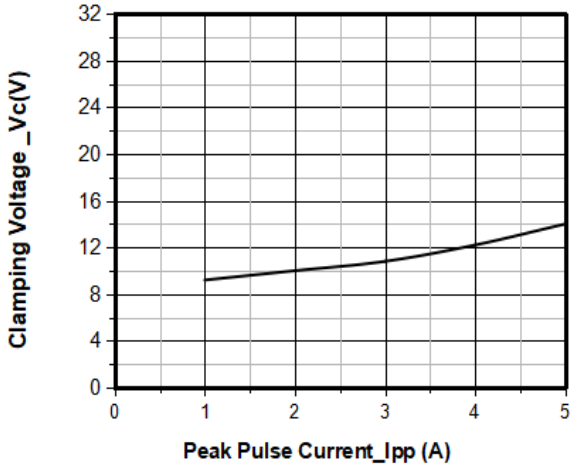
Typical Performance Characteristics (TA=25℃ unless otherwise Specified)



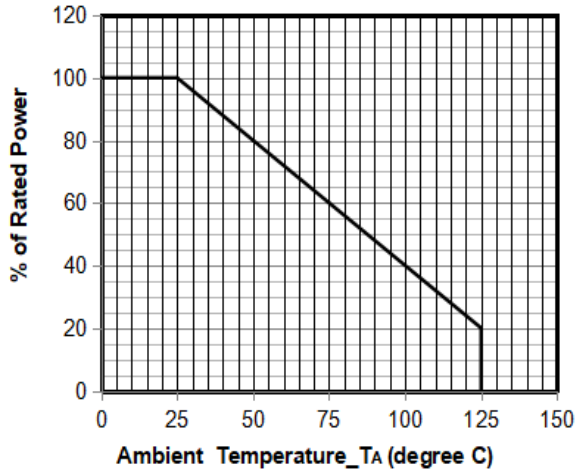
Junction Capacitance vs. Reverse Voltage



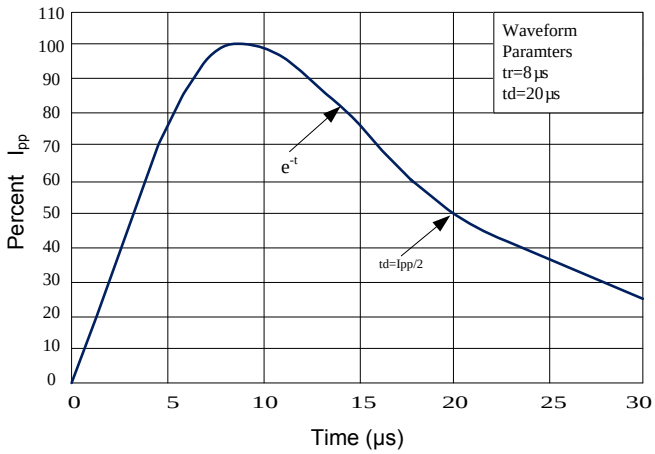
Peak Pulse Power vs. Pulse Time



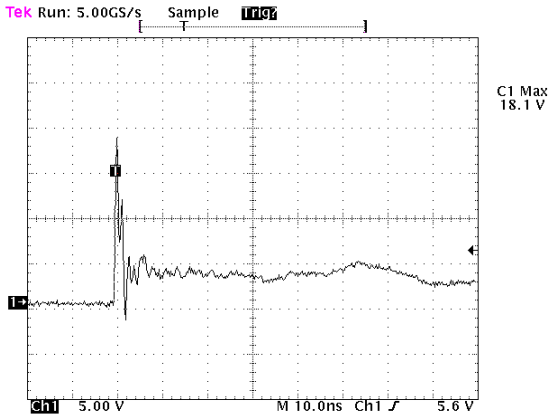
Clamping Voltage vs. Peak Pulse Current



Power Derating Curve



8 X 20μs Pulse Waveform

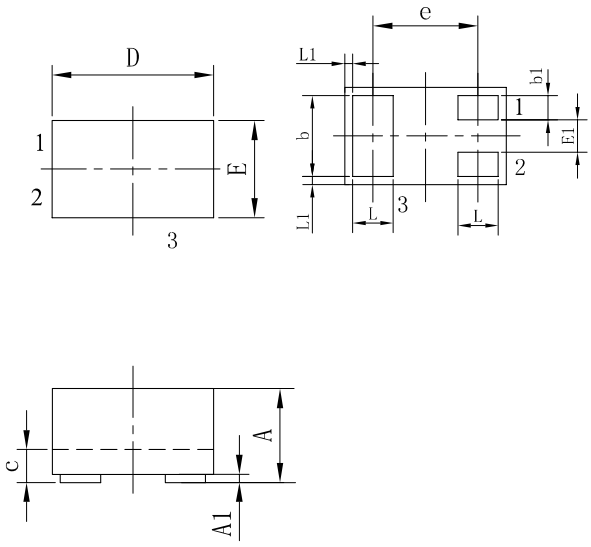


Note：Data is taken with a 10x attenuator

ESD Clamping Voltage

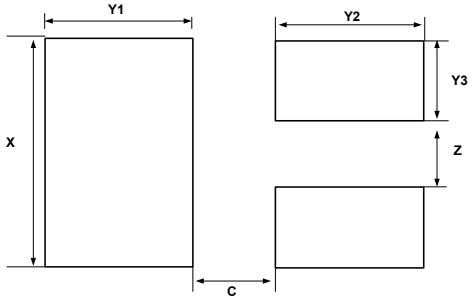
8 kV Contact per IEC61000−4−2

DFN1006-3 Package Outline Drawing



SYM	DIMENSIONS					
	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.45	0.50	0.55	0.018	0.020	0.022
A1	0.00	0.02	0.05	0.000	0.001	0.002
b	0.45	0.50	0.55	0.018	0.020	0.022
b1	0.10	0.15	0.20	0.004	0.006	0.008
c	0.12	0.15	0.18	0.005	0.006	0.007
D	0.95	1.00	1.05	0.037	0.039	0.041
e	0.65 BSC			0.026 BSC		
E	0.55	0.60	0.65	0.022	0.024	0.026
E1	0.15	0.20	0.25	0.006	0.008	0.010
L	0.20	0.25	0.30	0.008	0.010	0.012
L1	0.05 REF			0.0002 REF		

Suggested Land Pattern



SYM	DIMENSIONS	
	MILLIMETERS	INCHES
C	0.25	0.010
X	0.65	0.024
Y1	0.50	0.020
Y2	0.50	0.020
Y3	0.25	0.010
Z	0.20	0.008